2004 RCIQE International Seminar for 21st Century COE Program:

"Quantum Nanoelectronics for Meme-Media-Based **Information Technologies (II)**"

February 9th-11th, 2004 Conference Hall, Hokkaido University

日時: 平成16年 2月9日10:00 ~ 2月11日12:00

場所: 北海道大学学術交流会館

主催: 北海道大学21世紀COEプログラム(知識メディアを基盤とする次世代ITの研究)

北海道大学量子集積エレクトロニクス研究センター

	Pro	gram		
(Monday, Feb 10:00 - 10:10	ruary 9th) "Introductory Talk" Hideki Hasegawa, Hokkaido University	10:10 - 10:50	"MOVPE Growth of Nanostructures and Their Applications" Takashi Fukui, Hokkaido University	
	- Plenary -	10:50 - 11:10	Break	
10:10 - 10:50	"Meme Media for the Dynamic Federation of Web Applications and Ubiquitous Knowledge Resources" Yuzuru Tanaka, Hokkaido University	11:10 - 11:50	"A LSI Design of a High-Speed Wireless Communication System using Dynamic Reconfigurable Architecture" Yoshikazu Miyanaga, Kentarou Yoshikawa Yasuyuki	
10:50 - 11:10	Break		Hatakawa, Hokkaido University	
11:10 - 11:50	"Toward Realization of Intelligent Quantum Chips Utilizing III-V Nanoelectronics" Hideki Hasegawa, Hokkaido University	11:50 - 13:30	Lunch Break - Photonic Technologies -	
11:50 - 12:40	"Self-Assembled Quantum Dots for Optoelectronic Devices: Progress and Challenges" Mohamed Henini, Nottingham University	13:30 - 14:10	"Photonic Nanodevice Integration Engineering in Tokyo Tech" Shigehisa Arai, Tokyo Institute of Technology	
12:40 - 13:40	Lunch Break	14:10 - 14:50	"Challenges to Terahertz Integrated Circuits" Eiichi Sano, Hokkaido University	
12.40 14.20	- Spintronics -	14:50 - 15:10	·	
13:40 - 14:30	"Growth and Characterization of Ferromagnetic Metal/Compound Semiconductor Heterostructures for Spin Electronics" Chris Palmström, University of Minnesota		- GaN-Based Technologies -	
		15:10 - 15:50	"Surface Characterization and Passivation for GaN-Based Electron Devices"	
14:30 - 15:10	"High Efficiency Spin Injection from a Ferromagnetic Metal into a Semiconductor through		Tamotsu Hashizume, Hideki Hasegawa, Hokkaido University	
15:10 - 15:30	an Fe/InAs Junction" Kanji Yoh, Hokkaido University Break	15:50 - 16:30	"AlGaN/GaN Heterojunction FET for High Frequency Power Applications" Masaaki Kuzuhara, R&D Association for Future	
			Electron Devices	
15:30 - 16:20	"Hybrid Ferromagnetic (MnGa)As / GaAs- Structures: Metal Organic Vapor Phase Epitaxy, Structure Analysis and Magnetic Properties" Wolfgang Stolz, Philipps-University Marburg	16:30 - 18:00	Poster Viewing Session	
			Reception (Centennial Hall, Hokkaido University)	
		(Wednesday, February 11th)		
16:20 - 17:00	"Magnetoresistance and Magnetometory Phenomena in AlGaN/GaN Two-Dimensional	- GaN-Based Technologies (continued) -		
	Electron Gas"	9:30 -10:10	"Critical Issues for the Development of GaN-Based	
	Kotaro Tsubaki ¹ , N. Maeda ² , T. Saitoh ³ , N.		UV Devices" Hiroshi Amano, Meijo University	
	Kobayashi ⁴ , ¹ Toyo University, ² NTT Photonics	10:10 - 10:30	*	
	Laboratory, ³ NTT Basic Research Laboratory, ⁴ University of Electro-Communications		- Quantum Dots -	
	Oniversity of Electro-Communications	10:30 - 11:20	"In-rich InGaN/GaN Self-Assembled Quantum Dots by	
17:00 - 18:00	Lab Tour to RCIQE	10.50 11.20	MOCVD"	
(Tuesday, February 10th)			Euijoon Yoon, Seoul National University	
0.00 10.10	- Devices and Circuit Applications -	11:20 - 12:00	"Scanning Probe Microscopy Observations of	
9:30 - 10:10	"Room Temperature Operation of Highly Functional Single-Electron Transistors and Silicon		Electronic States and Work Functions in InAs Quantum Dots",	
	Nanocrystal Memories", Toshiro Hiramoto, M. Saitoh, I. Kim, University of		Arao Nakamura*, T. Yamauchi*, M. Tabuchi**, *Nagoya University and CREST-JST, **Nagoya	

聴講料無料、懇親会参加費 1,000円

Tokyo

Hokkaido

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